**Thyristor Module** 

## MCC44-16io1B

$V_{\text{RRM}}$	<i>=</i> 2x 1600 V					
I <sub>tav</sub>	=	49 A				
VT	=	1.34 V				

Phase leg

Part number

MCC44-16io1B







### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

## **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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## MCC44-16io1B

Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa	0 0	$T_{VJ} = 25^{\circ}C$			1700	
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward bl		$T_{vJ} = 25^{\circ}C$			1600	١
R/D	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{vJ} = 25^{\circ}C$			100	μ/
		V <sub>R/D</sub> = 1600 V	$T_{VJ} = 125^{\circ}C$			5	m/
V <sub>T</sub>	forward voltage drop	$I_{T} = 100 \text{ A}$	$T_{vJ} = 25^{\circ}C$			1.34	١
		$I_{T} = 200 \text{ A}$				1.75	١
		$I_{T} = 100 \text{ A}$	$T_{vJ} = 125^{\circ}C$			1.34	١
		I <sub>T</sub> = 200 A				1.80	١
I <sub>tav</sub>	average forward current	T <sub>c</sub> = 85°C	T <sub>vJ</sub> = 125°C			49	ļ
I <sub>T(RMS)</sub>	RMS forward current	180° sine				77	ł
V <sub>T0</sub>	threshold voltage		T <sub>v.i</sub> = 125°C			0.85	١
r <sub>T</sub>	slope resistance } for power lo	oss calculation only	vo			5.3	m۵
R <sub>thJC</sub>	thermal resistance junction to cas	6				0.53	K/W
R <sub>thCH</sub>	thermal resistance case to heatsi				0.20		K/W
	total power dissipation		$T_c = 25^{\circ}C$		0.20	180	N
-	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v,i} = 45^{\circ}C$			1.15	k/
TSM	max. Iorward burge burrent	t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			1.13	k/
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{v,i} = 125^{\circ}C$			980	~~ /
101	under for funcion	t = 8,3 ms; (60 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 1500}$			1.06	k/
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			6.62	ł
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			6.40	
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 125^{\circ}C$			4.80	kA²:
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			4.63	
C	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{vJ} = 25^{\circ}C$		54		pl
<b>P</b> <sub>GM</sub>	max. gate power dissipation	t <sub>P</sub> = 30 μs	$T_c = 125^{\circ}C$			10	W
		t <sub>P</sub> = 300 μs				5	N
P <sub>GAV</sub>	average gate power dissipation					0.5	V
(di/dt) <sub>cr</sub>	critical rate of rise of current	T <sub>vJ</sub> = 125 °C; f = 50 Hz re	epetitive, $I_T = 150 \text{ A}$			150	A/μ
		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu s; -$					
		$I_{G} = 0.45 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{DRM}$ no	on-repet., $I_{\tau} = 49 \text{ A}$			500	A/μ
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DBM}$	T <sub>v.i</sub> = 125°C			1000	V/µ
, ,,,		$R_{GK} = \infty$ ; method 1 (linear volta	ge rise)				
V <sub>gt</sub>	gate trigger voltage	$V_{\rm D} = 6 \text{ V}$	$T_{vJ} = 25^{\circ}C$			1.5	١
- 01	0 00 0		$T_{yJ} = -40 ^{\circ}\text{C}$			1.6	١
I <sub>GT</sub>	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			100	m/
■GT	gate ingger earrent	v <sub>D</sub> = 0 v	$T_{VJ} = -40^{\circ}C$			200	m/
V	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DBM}$	$T_{vJ} = -40^{\circ} \text{ C}$ $T_{vJ} = 125^{\circ} \text{ C}$			0.2	۱۱۱/
V <sub>gd</sub>		$\mathbf{v}_{\mathrm{D}} = 73 \mathbf{v}_{\mathrm{DRM}}$	$1_{VJ} = 125 \text{ C}$				i .
	gate non-trigger current		T 0500			10	m/
I.	latching current	$t_p = 10 \ \mu s$	$T_{vJ} = 25 \degree C$			450	m/
		$I_{\rm G} = 0.45 \text{A};  \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					1 1 1
I <sub>H</sub>	holding current	$V_{D} = 6 V R_{GK} = \infty$	$T_{vJ} = 25 \degree C$			200	m/
t <sub>gd</sub>	gate controlled delay time	$V_{D} = \frac{1}{2} V_{DRM}$	$T_{vJ} = 25 ^{\circ}C$			2	μ
		$I_{\rm G}~=~0.45{\rm A};~di_{\rm G}/dt=~0.45{\rm A}/\mu{\rm s}$					1 1 1
tq	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 120 \text{ A}; \text{ V} = \frac{2}{3}$	$\frac{1}{3} V_{\text{DRM}} = 100 \text{ °C}$		150		μ
		di/dt = 10 A/µs dv/dt = 20 V	/us_t_ = 200 us				   

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## MCC44-16io1B

Package TO-240AA						Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit		
	RMS current	per terminal					200	Α		
T <sub>vj</sub>	virtual junction temperature				-40		125	°C		
T <sub>op</sub>	operation temperature				-40		100	°C		
T <sub>stg</sub>	storage temperature				-40		125	°C		
Weight						81		g		
M <sub>D</sub>	mounting torque						4	Nm		
M <sub>T</sub>	terminal torque				2.5		4	Nm		
d <sub>Spp/App</sub>	croopago dictanco on curfac	e   striking distance through air	terminal to terminal	13.0	9.7			mm		
<b>d</b> <sub>Spb/Apb</sub>	creepage distance on surrac	e   Siriking distance ini ough an	terminal to backside	16.0	16.0			mm		
V	isolation voltage	t = 1 second			3600			V		
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V		



Date Code

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC44-16io1B	MCC44-16io1B	Box	36	452920

Similar Part	Package	Voltage class
MCMA50P1600TA	TO-240AA-1B	1600
MCMA65P1600TA	TO-240AA-1B	1600

Equiva	lent Circuits for	Simulation	* on die level	T <sub>vj</sub> = 125 °C
	⊢R₀−	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	4.1		mΩ

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## Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



sin

150

= 0.5 W

1.1.111

104

## Thyristor







Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

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## MCC44-16io1B

## Thyristor







liiju		•						
	d R <sub>t</sub>	<sub>hJC</sub> [K/W]						
	DC	0.53						
	180°	0.55						
	120°	0.58						
	60°	0.60						
	30°	0.62						
Constants for $Z_{thJC}$ calculation:								
i F	R <sub>thi</sub> [K/W	/] t <sub>i</sub> [s]						
1	0.015	0.0035						
2	0.026	0.0200						

0.1950

 $\mathbf{R}_{_{thJC}}$  for various conduction angles d:

3

0.489



0.8														-	- 1			60-				
												E	Ħ		Ŧ		-	120°		П		
Ζ <sub>thJK</sub>		╉┼		1		11-	T		Ø			H	Ħ		┦	T	N.	180°	H	Ħ		
0.6		╆┾	⊢	-	H	╉╟		₩	H		<u> </u>	$\vdash$	╫	_	+	+			++	+		
[K/W]		$\square$			Ц			4	Ш			$\square$	╨		$\downarrow$				Щ	4		
0.4												$\square$								Ш		
0.4							1															
0.2						K			Π			Π	Π			Π			Π			
0.2					R	Π			Π			Π	$\prod$						Π	Π		
0		$\square$		ľ					Π							Π			Π			
10	) <sup>-3</sup>		10 <sup>-2</sup>			10 <sup>-1</sup>				0⁰ [s]			10 <sup>1</sup>				10 <sup>2</sup>			10 <sup>3</sup>	I	
F	=ig. 10	Tran	sient	ther	mal	impe	edar	ice j			to h	eat	sink	(per	r thy	/ris	tor)					

d	R <sub>thJK</sub> [K/W]	
DC	0.73	
180°	0.75	
120°	0.78	
60°	0.80	
30°	0.82	
Constants	s for Z <sub>thuk</sub> calc	ulation:

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 ${\rm R}_{_{thJK}}$  for various conduction angles d:

		thJK - thJK
i	R <sub>thi</sub> [K/W]	t <sub>i</sub> [s]
1	0.015	0.0035
2	0.026	0.0200
3	0.489	0.0195
4	0.200	0.6800

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